

Advanced single shunt BLDC controller with embedded STM32 MCU



Features

- Extended operating voltage from 6.7 to 45 V
- · Three-phase gate drivers
 - 600 mA sink/source
 - Integrated bootstrap diodes
 - Cross-conduction prevention
- 32-bit ARM® Cortex®-M0 core:
 - Up to 48 MHz clock frequency
 - 4-kByte SRAM with HW parity
 - 32-kByte Flash memory with option bytes used for write/readout protection
 - Bootloader FW available
- 3.3. V DC/DC buck converter regulator with overcurrent, short-circuit, and thermal protection
- 12 V LDO linear regulator with thermal protection
- 20 general-purpose I/O ports (GPIO)
- 5 general-purpose timers
- 12-bit ADC converter (up to 9 channels)
- I²C, USART and SPI interfaces
- One rail-to-rail operational amplifier for signal conditioning
- Comparator for overcurrent protection with programmable threshold
- Standby mode for low power consumption
- UVLO protection on each power supply:
 - V_M , V_{DD} , V_{REG} and V_{BOOTx}
- On-chip debug support via SWD
- Extended temperature range: -40 to +125 °C

Product status link

STSPIN32F0B

Product summary				
Order Codes				
STSPIN32F0B	Tray			
STSPIN32F0BTR	Tape and Reel			
Marking	STSPIN32F0B			
Package	VFQFPN48 7x7x1mm			

Applications

- Power tools
- FANs and pumps
- · Industrial automation
- · Battery powered home appliances



1 Description

The STSPIN32F0B is a System-In-Package providing an integrated solution suitable for driving three-phase brushless motors using different driving modes.

It embeds a triple half-bridge gate driver able to drive power MOSFETs with a current capability of 600 mA (sink and source). The high- and low-side switches of same half-bridge cannot be simultaneously driven high thanks to an integrated interlocking function.

An internal DC/DC buck converter provides the 3.3 V voltage suitable to supply both the MCU and external components. An internal LDO linear regulator provides the supply voltage for gate drivers.

The integrated operational amplifier is available for the signal conditioning, e.g. the current sensing across the shunt resistor.

A comparator with a programmable threshold is integrated to perform the overcurrent protection.

The integrated MCU (STM32F031C6 with extended temperature range, suffix 7 version) allows performing field-oriented control, the 6-step sensorless and other advanced driving algorithms. It has the write-protection and read-protection feature for the embedded Flash memory to protect against unwanted writing and/or reading. It is possible to download the firmware on-the-field through the serial interface thanks to the embedded bootloader.

The STSPIN32F0B device also features overtemperature and undervoltage lockout protections and can be put in the standby mode to reduce the power consumption. The device provides 20 general-purpose I/O ports (GPIO) with the 5 V tolerant capability, one 12-bit analog-to-digital converter with up to 9 channels performing conversions in a single-shot or scan modes, 5 synchronizable general-purpose timers and supports an easy to use debugging serial interface (SWD).

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2 Block diagrams

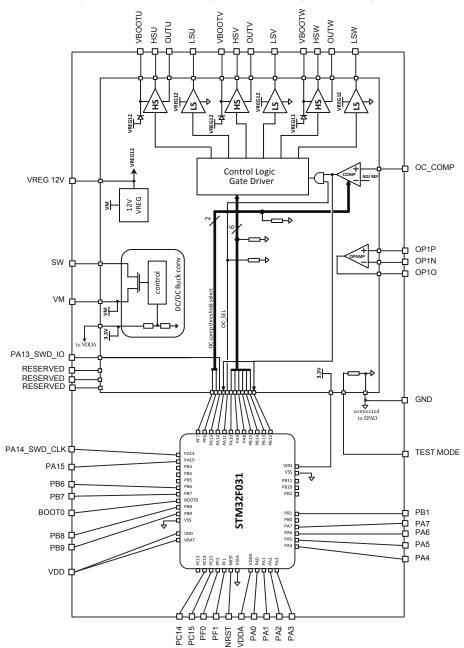


Figure 2. STSPIN32F0B System-In-Package block diagram

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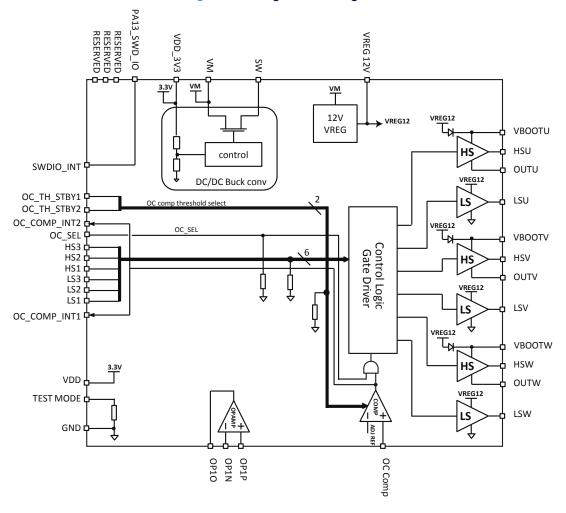


Figure 3. Analog IC block diagram

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3 Electrical data

3.1 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in Table 1. Absolute maximum ratings may cause permanent damage to the device. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 1. Absolute maximum ratings

Symbol	Parameter	Test condition	Value	Unit	
V _M	Power supply voltage	-	-0.3 to 48	V	
V _{REG12}	Linear regulator output and gate driver supply voltage	VREG12 shorted to VM	15	V	
V _{OPP}	Op amp positive input voltage	-	-0.2 to V _{DD} + 0.2	V	
V _{OPN}	Op amp negative input voltage	-	-0.2 to V _{DD} + 0.2	V	
V _{CP}	Comparator input voltage	-	-2 to 2	V	
V_{HS}	High-side gate output voltage	-	V _{OUT} - 0.3 to V _{BOOT} + 0.3	V	
V _{LS}	Low-side gate output voltage	-	-0.3 to V _{REG12} + 0.3	V	
V _{BOOT}	Bootstrap voltage	-	Max. (V _{OUT} - 0.3 or -0.3) to min. ('V _{OUT} + V _{REG12} + 0.3' or 60)	V	
V _{OUT}	Output voltage (OUTU, OUTV, OUTW)	-	-2 to V _M + 2	V	
dV _{OUT} /dt	Output slew rate	-	± 10	V/ns	
		TTa type (1)	-0.3 to 4		
V_{IO}	MCU logic input voltage ⁽¹⁾	FT, FTf type ⁽¹⁾	-0.3 to V _{DD} + 4 ⁽²⁾	V	
		BOOT0	0 to 9.0		
I _{IO}	MCU I/O output current	(1)	-25 to 25	mA	
ΣI _{IO}	MCU I/O total output current	, (3) (1)	-80 to 80	mA	
V_{DD}	MCU digital supply voltage	(1)	-0.3 to 4	V	
V_{DDA}	MCU analog supply voltage	(1)	-0.3 to 4	V	
T _{stg}	Storage temperature	-	-55 to 150	°C	
Tj	Operating junction temperature	-	-40 to 150	°C	

^{1.} See Table 15 Voltage characteristics in the STM32F031C6 datasheet (suffix 7 version).

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^{2.} Valid only if the internal pull-up/pull-down resistors are disabled. If internal the pull-up or pull-down resistor is enabled, the maximum limit is 4 V.

If the MCU supply voltage is provided by an integrated DC/DC regulator, the application current consumption is limited at I_{DDA,max} value (see Table 5. Electrical characteristics).



3.2 ESD protections

Table 2. ESD protection ratings

Symbol	Parameter	Test condition	Class	Value	Unit
НВМ	Human body model	Conforming to ANSI/ESDA/JEDEC JS-001-2014	H2	2	kV
CDM	Charge device model	Conforming to ANSI/ESDA/JEDEC JS-002-2014	C2	750	V

3.3 Recommended operating conditions

Table 3. Recommended operating conditions

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
V _M	Power supply voltage	-	6.7 (1)	-	45	V
dV _M /dt	Power supply voltage slope	V _M = 45 V	-	-	0.75	V/µs
V_{DDA}	DC/DC regulator output voltage	-	-	3.3	-	V
L _{SW}	Output inductance	-	-	22	-	μH
C _{DDA}	Output capacitance	-	47	-	-	μF
ESR _{DDA}	Output capacitor ESR	-	-	-	200	mΩ
V	Lieuwani daka auta da aka da aka aka aka aka aka aka aka	13 < V _M < 45 V	-	12	-	V
V _{REG12}	Linear regulator output and gate driver supply voltage	Shorted to VM	6.7 ⁽¹⁾	-	15	V
C _{REG}	Load capacitance	-	1	10	-	μF
ESR _{REG}	ESR load capacitance	-	-	-	1.2	Ω
V _{BO}	Floating supply voltage (2)	-	-	V _{REG12} - 1	15	V
V _{CP}	Comparator input voltage	-	0	-	1	V
т.	Operating junction temperature	Analog IC	-40	-	125	°C
T _j	Operating junction temperature	MCU (3)	-40	-	125	°C

^{1.} UVLO threshold V_{MOn_max}.

3.4 Thermal data

Thermal values are calculated by simulation with the following boundary conditions: 2s2p board as per the std. JEDEC (JESD51-7) in natural convection, board dimensions: $114.3 \times 76.2 \times 1.6 \, \text{mm}$, ambient temperature: $25 \, ^{\circ}\text{C}$.

Table 4. Thermal data

Symbol	Parameter	Value	Unit
R _{th (JA)}	Thermal resistance junction to ambient	45.6	°C/W

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^{2.} $V_{BO} = V_{BOOT} - V_{OUT}$.

^{3.} See the STM32F031C6 datasheet (suffix 7 version).



4 Electrical characteristics

Testing conditions: V_M = 15 V; V_{DD} = 3.3 V, unless otherwise specified.

Typical values are tested at T_j = 25 °C, minimum and maximum values are guaranteed by thermal characterization in the temperature range of -40 to 125 °C, unless otherwise specified.

Table 5. Electrical characteristics

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
Power supp	ly and standby mode	•				
		V _M = 45 V; V _{DD} = 3.5 V externally supplied	-	2	2.6	mA
I_{M}	V _M current consumption	Standby PF7 = '0' PF6 = '0'		000	1100	μА
		V_M = 45 V; V_{DD} = 3.5 V externally supplied	-	880		
V_{MOn}	V _M UVLO turn-on threshold	V _M rising from 0 V	6.0	6.3	6.6	V
V_{MOff}	V _M UVLO turn-off threshold	V _M falling from 8 V	5.8	7.1	6.4	V
V_{MHys}	V _M UVLO threshold hysteresis	-	-	0.2	-	V
		V _{DD} = 3.5 V externally supplied	-	2.5	5	
I_{DD}	V _{DD} current consumption	Standby PF7 = '0' PF6 = '0'		0.5	5	mA
		V _{DD} = 3.5 V externally supplied	-	2.5	J	
		V _{DD} = 3.5 V externally supplied	-	400	550	
I_{DDA}	V _{DDA} current consumption	Standby PF7 = '0' PF6 = '0'	_	80	125	μA
		V _{DD} = 3.5 V externally supplied				
V_{DDOn}	V _{DD} UVLO turn-on threshold	V _{DD} rising from 0 V	2.5	2.65	2.8	V
V_{DDOff}	V _{DD} UVLO turn-off threshold	V _{DD} falling from 3.3 V	2.2	2.35	2.5	V
V_{DDHys}	V _{DD} UVLO threshold hysteresis	-	-	0.3	-	V
	V _{REG} current consumption	V_{REG} = 13 V externally supplied, V_{M} = 45 V;	_	800	1200	
I _{REG12}		no commutation		000		μA
		Standby PF7 = '0' PF6 = '0' V _{REG} = 13 V externally supplied	-	800	1200	·
$V_{REG12On}$	V _{REG12} UVLO turn-on threshold	V _{REG12} rising from 0 V	6.0	6.3	6.6	V
V _{REG12Off}	V _{REG12} UVLO turn-off threshold	V _{REG12} falling from 8 V	5.8	6.1	6.4	V
V _{REG12Hys}	V _{REG12} UVLO threshold hysteresis	-	-	0.25	-	V
I _{BOOT}	V _{BO} current consumption	HS on, V _{BO} = 13 V	-	200	290	μA
V _{BOOn}	V _{BO} UVLO turn-on threshold	V _{BO} rising from 0 V	5.5	5.8	6.1	V
V_{BOOff}	V _{BO} UVLO turn-off threshold	V _{BO} falling from 8 V	5.3	5.6	5.9	V
V _{BOHys}	V _{BO} UVLO threshold hysteresis	-	-	0.15	-	V
t _{sleep}	Standby set time	-	-	-	1	μs
DC/DC swite	ching regulator	'				1
V _{PWR_OK}	Power good voltage	-	5.6	6	6.4	V
V_{DDA}	Average output voltage		3.09	3.3	3.5	V
I _{DDA}	Output current	DC; MCU current consumption included	-	-	70	mA

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Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
		Open loop, V _{DDA} floating				
f_{SW}	Maximum SW switching frequency	I _{SW} = 100 mA	-	200	330	kHz
R _{SWDS(ON)}	Switch ON resistance	I _{SW} = 200 mA	-	1.4	-	Ω
η	Efficiency	V _M = 8 V; I _{DDA} = I _{DDA,max}	-	80	-	%
I _{SW,peak}	Peak current threshold	-	-	320	-	mA
lovc	Latched overcurrent threshold	-	-	1	-	Α
t _{SS}	Soft-start time	-	2.5	5	7.5	ms
Linear regula	ator			1		
	Linear regulator output and gate driver supply	V _M = 13 ÷ 45 V ⁽³⁾		40	10.0	
V _{REG12}	voltage	I _O = 10 mA	11.4	12	12.6	V
V _{REG12,drop}	Drop voltage	V _M = 8 ÷ 11 V, I _O = 10 mA	-	200	400	mV
I _{REG12,lim}	Linear regulator current limit	V _M = 13 V	20	-	40	mA
Gate drivers						
I _{SI}	Mayirana airl/acurae aurrent canabilities	T _J = 25 °C	400	600	-	mA
I_{SO}	Maximum sink/source current capabilities	Full temperature range	350	-	-	mA
R _{PDin}	Input lines pull-down resistor	-	30	60	95	kΩ
t _{on}	Input-to-output propagation delay (4)	-	_	20	40	ns
t_{off}	imput-to-output propagation delay			20	40	115
MT	Delay matching, HS and LS turn-on/off (5)	-	-	10	20	ns
R _{DS_diode}	Bootstrap diode ON resistance	-	-	120	240	Ω
Operational	amplifier		·			
V _{icm}	Input common mode voltage range	-	-0.1	-	V _{DD} + 0.1	V
V	Innuit officet voltage	V _{out} = 1.65; T _j = 25 °C	-	1	6	mV
V_{OPio}	Input offset voltage	V _{out} = 1.65; full temp. range	-	-	7	mV
I _{OPio}	Input offset current	V _{out} = 1.65	-	-	100	pA
l _{OPib}	Input bias current		-	-	100	pA
CMRR	Common mode rejection ratio	0 to 3.3 V; V _{out} = 1.65 V	70	90	-	dB
A _{OL}	Open loop gain	R _L = 10 kΩ; V _{out} = 1.65	-	90	-	dB
V _{DD} - V _{OH}	High level output voltage	R _L = 10 kΩ	-	15	40	mV
V _{OL}	Low level output voltage	R _L = 10 kΩ	-	15	40	mV
		V _{out} = 3.3 V; T _j = 25 °C	18	-	-	mA
	Sink output current	V _{out} = 3.3 V; full temp. range	16	-	-	
l _{OUT}		V _{out} = 0 V; T _j = 25 °C	18	-	-	mA
	Source output current	V _{out} = 0 V; full temp. range	16	-	-	
		R _L = 2 kΩ; C _L = 100 pF				
GBP	Gain bandwidth product	V _{out} = 1.65	10	18	-	MHz
		Phase margin = 45°		_		
Gain	Minimum gain for stability	0.2 V < V _{out} < V _{DD} - 0.2	-	4	-	V/V

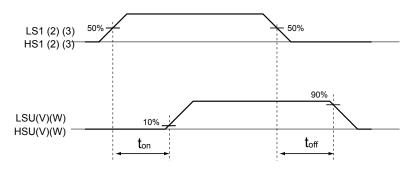
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Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
SR	Olaverata	R _L = 2 kΩ; C _L = 100 pF		10		\//ua
SK	Slew rate	V _{in} 1 to 2 V step	-	10	-	V/µs
OC compara	ator					
		PF6 = '0' PF7 = '1'	90	100	120	mV
OC _{th}	Overcurrent threshold	PF6 = '1' PF7 =' 0'	235	255	275	mV
		PF6 = '1' PF7 = '1'	465	505	545	mV
t _{CPD}	Comparator propagation delay	OC _{th} = 0.5 V;	_	80	120	ns
CPD	Comparator propagation delay	OC_Comp: voltage step from 0 to 1 V	_	80	120	115
t _{OCdeglitch}	Comparator input deglitch filter time		35	50	-	ns
t _{OCrelease}	Minimum overcurrent latch release pulse width		-	-	20	ns
Thermal pro	tection					
T _{SD}	Thermal shut-down temperature	-	130	140	150	°C
T _{hys}	Thermal shut-down hysteresis	-	20	30	40	°C

- 1. The current consumption depends on the firmware loaded in the microcontroller.
- Using the 47 μF capacitor (APXG250ARA470MF61G), 22 μH inductor (MLF1608C220KTA00), and diode 1N4448TR.
- 3. With 11 < V_M < 13 V the linear output voltage can be VREG12 or 'VM-VREG12,drop' depending on the linear regulator is already turned-on or not.
- 4. See Figure 4. Gate drivers timing
- 5. $MT = max. \; (|t_{on(LVG)} t_{off(LVG)}|, \; |t_{on(HVG)} t_{off(HVG)}|, \; |t_{off(LVG)} t_{on(HVG)}|, \; |t_{off(HVG)} t_{on(LVG)}|).$
- 6. Guaranteed by design.
- 7. Guaranteed by I_{OUT} test.
- 8. See Figure 17. Driver logic overcurrent management signals.

Figure 4. Gate drivers timing



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5 Pin description

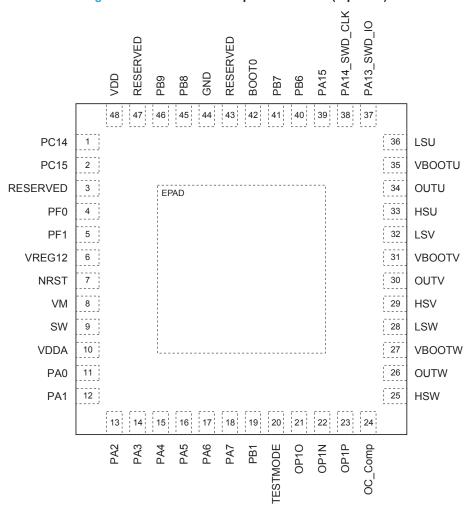


Figure 5. STSPIN32F0B SiP pin connection (top view)

Table 6. STSPIN32F0B SiP pin description

No.	Name	Туре	Function
1	PC14	GPIO	MCU PC14
2	PC15	GPIO	MCU PC15
3	RESERVED	-	Reserved for test mode
4	PF0	GPIO	MCU PF0
5	PF1	GPIO	MCU PF1
6	VREG12	Power	12 V linear regulator output
7	NRST	GPIO	MCU reset pin
8	VM	Power	Power supply voltage (bus voltage)
9	SW	Analog out	3.3 V DC/DC buck regulator switching node
10	VDDA	Power	MCU analog power supply voltage
11	PA0	GPIO	MCU PA0

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No.	Name	Туре	Function	
12	PA1	GPIO	MCU PA1	
13	PA2	GPIO	MCU PA2	
14	PA3	GPIO	MCU PA3	
15	PA4	GPIO	MCU PA4	
16	PA5	GPIO	MCU PA5	
17	PA6	GPIO	MCU PA6	
18	PA7	GPIO	MCU PA7	
19	PB1	GPIO	MCU PB1	
20	TESTMODE	Digital In	Test mode input	
21	OP1O	Analog out	Operational amplifier output	
22	OP1N	Analog in	Operational amplifier inverting input	
23	OP1P	Analog in	Operational amplifier non-inverting input	
24	OC_COMP	Analog in	Overcurrent comparator input	
25	HSW	Analog out	W phase high-side driver output	
26	OUTW	Power	W phase high-side (floating) common voltage	
27	VBOOTW	Power	W phase bootstrap supply voltage	
28	LSW	Analog out	W phase low-side driver output	
29	HSV	Analog out	V phase high-side driver output	
30	OUTV	Power	V phase high-side (floating) common voltage	
31	VBOOTV	Power	V phase bootstrap supply voltage	
32	LSV	Analog out	V phase low-side driver output	
33	HSU	Analog out	U phase high-side driver output	
34	OUTU	Power	U phase high-side (floating) common voltage	
35	VBOOTU	Power	U phase bootstrap supply voltage	
36	LSU	Analog out	U phase low-side driver output	
37	PA13_SWD_IO	GPIO	MCU PA13/SWDIO (system debug data via analog IC)	
38	PA14_SWD_CLK	GPIO	MCU PA14/SWDCLK (system debug clock)	
39	PA15	GPIO	MCU PA15	
40	PB6	GPIO	MCU PB6	
41	PB7	GPIO	MCU PB7	
42	воото	Digital in	MCU BOOT0	
43	RESERVED	-	Reserved for test mode (can be left floating in application)	
44	GND	Power	Ground	
45	PB8	GPIO	MCU PB8	
46	PB9	GPIO	MCU PB9	
47	RESERVED	-	Reserved for test mode	
48	VDD	Power	MCU digital power supply	
	EPAD	Power	Internally connected to ground	

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Table 7. STSPIN32F0B MCU pad mapping

MCU pad	Туре	Analog IC pad	Alternate and additional functions
PC14	I/O - TC	-	OSC32_IN
PC15	I/O - TC	-	OSC32_OUT
PF0	I/O - FT	-	OSC_IN
PF1	I/O - FT	-	OSC_OUT
NRST	I/O - RST	-	Device reset input / internal reset output (active low)
VDDA	S	VDD_3V3	Analog power supply voltage
DAO	1/O TT-		TIM2_CH1_ETR, USART1_CTS
PA0	I/O - TTa	-	ADC_IN0, RTC_TAMP2, WKUP1
PA1	I/O - TTa		TIM2_CH2, EVENTOUT, USART1_RTS
FAI	1/O - 1 1a	_	ADC_IN1
PA2	I/O - TTa	_	TIM2_CH3, USART1_TX
TAL	1/0 - 110	_	ADC_IN2
PA3	I/O - TTa	_	TIM2_CH4, USART1_RX
	#0 Ha		ADC_IN3
PA4	I/O - TTa	_	SPI1_NSS, I2S1_WS, TIM14_CH1, USART1_CK
			ADC_IN4
PA5	I/O - TTa	_	SPI1_SCK, I2S1_CK, TIM2_CH1_ETR
·			ADC_IN5
DAG	1/O TT-		SPI1_MISO, I2S1_MCK, TIM3_CH1, TIM1_BKIN, TIM16_CH1, EVENTOUT
PA6	I/O - TTa	-	ADC_IN6
			TIM3_CH4, TIM14_CH1, TIM1_CH3N
PB1	I/O - TTa	-	ADC_IN9
			SPI1_MOSI, I2S1_SD, TIM3_CH2, TIM14_CH1,
PA7	I/O - TTa	-	TIM1_CH1N, TIM17_CH1, EVENTOUT
			ADC_IN7
PB12	I/O - FT	OC_COMP_INT	TIM1_BKIN (1)
PB13	I/O - FT	LS1	TIM1_CH1N ⁽¹⁾
PB14	I/O - FT	LS2	TIM1_CH2N ⁽¹⁾
PB15	I/O - FT	LS3	TIM1_CH3N ⁽¹⁾
PA8	I/O - FT	HS1	TIM1_CH1 ⁽¹⁾
PA9	I/O - FTf	HS2	TIM1_CH2 ⁽¹⁾
PA10	I/O - FTf	HS3	TIM1_CH3
PA11	I/O - FT	OC_SEL	Push-pull output ⁽¹⁾
PA12	I/O - FT	OC_COMP_INT2	TIM1_ETR ⁽¹⁾
PA13_SWD_IO	I/O - FT	SWDIO_INT	IR_OUT, SWDIO
PF6	I/O - FTf	OC_TH_STBY2	Push-pull output ⁽¹⁾
PF7	I/O - FTf	OC_TH_STBY1	Push-pull output ⁽¹⁾
PA14_SWD_CLK	I/O - FT	-	USART1_TX, SWCLK
PA15	I/O - FT	-	SPI1_NSS, I2S1_WS, TIM2_CH_ETR, EVENTOUT, USART1_RX

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MCU pad	Туре	Analog IC pad	Alternate and additional functions
PB6	I/O - FTf	-	I2C1_SCL, USART1_TX, TIM16_CH1N
PB7	I/O - FTf	-	I2C1_SDA, USART1_RX, TIM17_CH1N
PB8	I/O - FTf	-	I2C1_SCL, TIM16_CH1
PB9	I/O - FTf	-	I2C1_SDA, TIM17_CH1
VBAT, VDD	S	VDD	Backup and digital power supply
VSS, VSSA	S	-	Ground
BOOT0	I	-	Boot memory selection
PC15, PB0, PB2, PB10, PB11, PA15, PB3, PB4, PB5	-	-	Not connected

The analog IC is designed to support these GPIOs configuration only. Different configuration could cause device malfunctioning. The GPIO input configuration without pull-up or pull-down is always allowed.

Note: Each unused GPIO inside the SiP should be configured in the OUTPUT mode low level after the startup by software.

Table 8. STSPIN32F0B analog IC pad description

Pinout name	Pad name	Type	Function
PA13_SWD_IO	SYS_SWDIO	Digital I/O	System debug data (connected to the output through the analog IC)
VDDA	VDD_3V3	Power	3.3 V DC/DC buck regulator voltage output
VM	VM	Power	Power supply voltage (bus voltage)
SW	SW	Analog out	3.3 V DC/DC buck regulator switching node
VREG12	VREG12	Power	12 V linear regulator output
VBOOTU	VBOOTU	Power	U phase bootstrap supply voltage
HSU	HSU	Analog out	U phase high-side driver output
OUTU	OUTU	Power	U phase high-side (floating) common voltage
LSU	LSU	Analog out	U phase low-side driver output
VBOOTV	VBOOTV	Power	V phase bootstrap supply voltage
HSV	HSV	Analog out	V phase high-side driver output
OUTV	OUTV	Power	V phase high-side (floating) common voltage
LSV	LSV	Analog out	V phase low-side driver output
VBOOTW	VBOOTW	Power	W phase bootstrap supply voltage
HSW	HSW	Analog out	W phase high-side driver output
OUTW	OUTW	Power	W phase high-side (floating) common voltage
LSW	LSW	Analog out	W phase low-side driver output
OC_Comp	OC_COMP	Analog in	Overcurrent comparator input
OP1P	OP1P	Analog out	Op amp 1 output
OP1N	OP1N	Analog in	Op amp 1 inverting input
OP10	OP1O	Analog in	Op amp 1 non-inverting input
RESERVED	RESERVED	-	Reserved for test mode
RESERVED	RESERVED	-	Reserved for test mode
RESERVED	RESERVED	-	Reserved for test mode
GND	GND	Power	Ground

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Pinout name	Pad name	Туре	Function
TESTMODE	TESTMODE	Digital in	Test mode input
-	VDD	Power	MCU digital power supply
-	OC_COMP_INT	Digital out	OC comparator output
-	HS1	Digital in	High-side input driver U
-	HS2	Digital in	High-side input driver V
-	HS3	Digital in	High-side input driver W
-	LS1	Digital in	Low-side input driver U
-	LS2	Digital in	Low-side input driver V
-	LS3	Digital in	Low-side input driver W
-	OC_SEL	Digital in	OC protection selection
-	OC_COMP_INT2	Digital out	OC comparator output
-	SWD_IO_INT	Digital in	System debug data (connected to the output through the analog IC)
-	OC_TH_STBY1	Digital in	Overcurrent threshold selection and standby input 1
-	OC_TH_STBY2	Digital in	Overcurrent threshold selection and standby input 2

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6 Device description

The STSPIN32F0B is a System-In-Package providing an integrated solution suitable for driving the three-phase BLDC motors.

6.1 UVLO and thermal protections

Table 9. UVLO and OT protection management summarizes the UVLO and OT protection management.

V_M UVLO V_{DD} UVLO V_{REG12} UVLO **Block V_{BOOT} UVLO** Lin. Reg OT DC/DC Reg OT DC/DC regulator OFF Linear regulator OFF OFF OFF Op amps and OC comp OFF OFF LOW, (2) (1) HSU, HSV, HSW output LOW LOW LOW (1) LSU, LSV, LSW output LOW LOW LOW⁽¹⁾

Table 9. UVLO and OT protection management

^{2.} Only the high-side gate driver in which the UVLO condition is detected (e.g. UVLO on VBOOTU causes the HSU turning off).

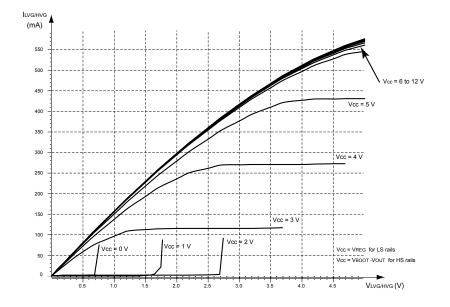


Figure 6. Gate drivers' outputs characteristics in UVLO conditions

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^{1.} The N-channel of the gate driver is turned ON with all the available supply voltage, refer to Figure 6. Gate drivers' outputs characteristics in UVLO conditions.



6.1.1 UVLO on supply voltages

The STSPIN32F0B device provides UVLO protections on all power supplies.

The device enters into the undervoltage condition when the power supply voltage falls below the off threshold voltage and expires when the motor supply voltage goes over the on threshold voltage.

Table 9. UVLO and OT protection management shows the UVLO protection management: which blocks are switched off after an UVLO event.

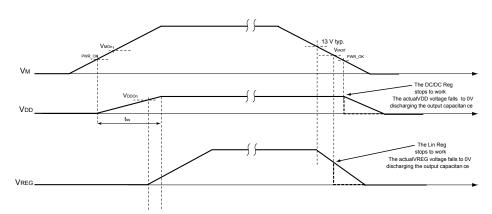


Figure 7. Power-up and power-down sequence

6.1.2 Thermal protection

The device embeds an overtemperature shut-down protection. The thermal sensors are placed next to the DC/DC and linear regulator blocks.

When the OT protection is triggered the correspondent block is switched off, the thermal shut-down condition only expires when the temperature goes below the " T_{SD} - T_{hys} " temperature (auto-restart).

Table 9. UVLO and OT protection management shows the thermal protection management which blocks are switched off after an overtemperature event.

6.2 DC/DC buck regulator

The internal DC/DC buck converter provides the 3.3 V supply voltage suitable to supply the MCU and other external devices.

The regulator operates in the discontinuous current mode (DCM).

A soft-start function with fixed start-up time is implemented to minimize the inrush current at the start-up, refer to Figure 9. Soft-start timing.

An overcurrent and short-circuit protection is provided.

If a failure event occurs on the SW pin, the regulator is latched off. To restart the DC/DC regulator a power-down and power-up cycle of device supply voltage (V_M) is needed.

If a failure event occurs on the regulator output (VDDA pin) and the voltage goes below the UVLO threshold (V_{DDOff}), the regulator restarts with a new soft-start sequence until the OC condition is removed. In this case the current in the coil is limited by $I_{SW,peak}$.

The DC/DC regulator embeds a thermal protection as described in Section 6.1.2 Thermal protection.

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To MCU

CVDDA

VDDA

VDDA

VDDA

SW

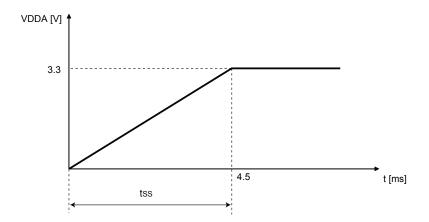
VM

Control

DC/DC buck conv.

Figure 8. DC/DC buck regulator topology

Figure 9. Soft-start timing



6.2.1 External optional 3.3 V supply voltage

It is possible provide externally the $3.3\ V$ supply voltage directly on the VDDA pin. In this case, there are two possible configurations:

- The SW pin floating or shorted to VM: in this case the internal power switch of the DC/DC converter continues to switch on/off according to the internal clock
- 2. The SW pin shorted to GND or VDD: in this case the internal power switch detects a short-circuit and it is latched off.

Note: It is not allowed to apply VDD voltage externally in case of VM < VDD.

6.3 Linear regulator

The internal 12 V linear regulator is a LDO regulator providing the supply voltage for the gate drivers section. An external capacitor connected to the VREG12 pin is required.

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VREG12

VREG12

VREG12

VREG12

Figure 10. Linear regulator block diagram

When the VM voltage is below to 12 V, the VM pin and the linear regulator output can be shorted together providing the gate driver supply externally.

The linear regulator embeds a thermal protection as described in Section 6.1.2 Thermal protection.

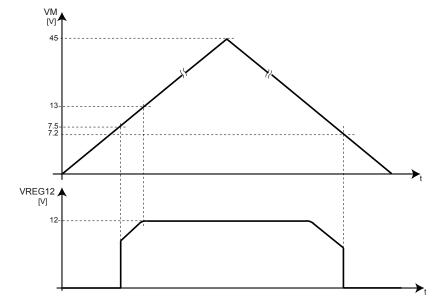


Figure 11. Linear regulator output characteristics

Note: The linear regulator is designed to supply the internal circuitry only and must not be used to supply external components.

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6.4 Standby mode

The device is forced into the standby mode to reduce power consumption forcing both the OC_TH_STBY1 and OC_TH_STBY2 analog IC inputs low (see Table 12. OC threshold values).

When the standby mode is set the analog IC is put into the low consumption mode after a t_{sleep} time, in particular:

- · The linear regulator is switched off
- · All the output drivers are forced low (external power switches turned off)
- · Op amps and comparators disabled
- The DC/DC regulator remains operative.

When the device exits from the standby mode a set time is necessary to recover a proper value of the 12 V internal regulator. This set time is strictly dependent by the capacitor connected on the VREG12 pin and can be calculated with Equation 1.

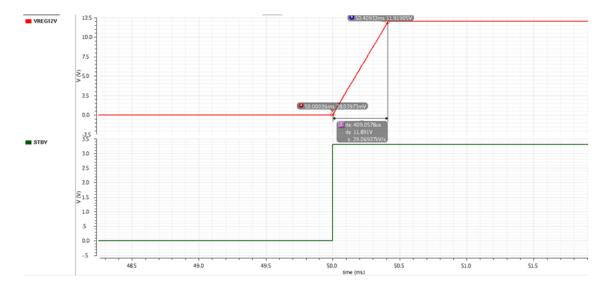


Figure 12. "Standby to normal" operation timing ($C_{REG} = 1 \mu F$)

Equation 1

$$t_{REG} = \frac{C_{REG} \cdot V_{REG12}}{I_{REG12, lim}} \tag{1}$$

6.5 Gate drivers

The STSPIN32F0B device integrates a triple half-bridge gate driver able to drive N-channel power MOSFETs or IGBTs. The high-side section is supplied by a bootstrapped voltage technique with an integrated bootstrap diode.

All the input lines (refer to Figure 3. Analog IC block diagram) are connected to

a pull-down resistor (60 $k\Omega$ typical value) to guarantee the low logic level during the device start-up and when the MCU lines are not present.

The high- and low-side outputs of same half-bridge cannot be simultaneously driven high thanks to an integrated interlocking function.

6.6 Microcontroller unit

The integrated MCU is the STM32F031C6 with following main characteristics:

- Core: ARM[®] 32-bit Cortex[™]-M0 CPU, frequency up to 48 MHz
- Memories: 4kB of SRAM, 32 kB of Flash memory
- · CRC calculation unit
- Up to 20 fast I/Os

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- Advanced-control timer dedicated for PWM generation
- Up to 5 general purpose timers
- 12-bit ADC (up to 9 channels)
- Communication interfaces: I²C, USART, SPI
- Serial wire debug (SWD)
- Extended temperature range: -40 to 125 °C

For more details refer to the STM32F031C6 datasheet on www.st.com

6.6.1 Memories and boot mode

The device has the following features:

- 4 Kbytes of the embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states and featuring embedded parity checking with an exception generation for fail-critical applications.
- The non-volatile memory is divided into two arrays:
 - 32 Kbytes of the embedded Flash memory for programs and data
 - Option bytes

The option bytes are used to write-protect the memory (with 4 KB granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no readout protection
- Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or the boot in the RAM is selected
- Level 2: chip readout protection, debug features (Cortex-M0 serial wire) and the boot in the RAM selection disabled.

At startup the BOOT0 pin and the boot selector option bit are used to select one of the three boot options:

- · Boot from user Flash memory
- Boot from system memory
- Boot from embedded SRAM

The boot loader is located in the system memory. It is used to reprogram the Flash memory by using USART on pins PA14/PA15.

The main Flash memory is aliased in the boot memory space (0x00000000), but still accessible from its original memory space (0x08000000). In other words, the Flash memory contents can be accessed starting from the address 0x00000000 or 0x08000000.

6.6.2 Power management

The VDD pin is the power supply for the I/Os and the internal regulator.

The VDDA pin is the power supply for the ADC, reset blocks, RCs and PLL. The V_{DDA} voltage can be generated through the internal DC/DC buck converter, otherwise it is possible to provide externally the supply voltage directly on the VDDA pin.

Note: The VDDA voltage level must be always greater or equal to the VDD voltage level and must be established first.

The MCU has integrated power-on reset (POR) and power-down reset (PDR) circuits. They are always active, and ensure proper operation above a threshold of 2 V. The device remains in the reset mode when the monitored supply voltage is below a specified threshold.

- The POR monitors only the V_{DD} supply voltage. During the startup phase it is required that V_{DDA} should arrive first and be greater than or equal to V_{DD}.
- The PDR monitors both the V_{DD} and V_{DDA} supply voltages, however the V_{DDA} power supply supervisor can be disabled (by programming a dedicated option bit) to reduce the power consumption if the application design ensures that V_{DDA} is higher than or equal to V_{DD}.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD} drops below the V_{PVD} threshold

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and/or when V_{DD} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

The MCU supports three low-power modes to achieve the best compromise between low-power consumption, short start-up time and available wake-up sources:

Sleep mode

 In the sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake-up the CPU when an interrupt/event occurs.

· Stop mode

- The stop mode achieves very low-power consumption while retaining the content of the SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in the normal or in the low-power mode.
- The device can be woken-up from the stop mode by any of the EXTI lines (one of the 16 external lines, the PVD output, RTC, I²C1 or USART1).

Standby mode

- The standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering the standby mode, SRAM and register contents are lost except for registers in the RTC domain and standby circuitry.
- The device exits the standby mode when an external reset (NRST pin), an IWDG reset,
- a rising edge on the WKUP pins, or an RTC event occurs.

6.6.3 High-speed external clock source

The high-speed external (HSE) clock can be generated from the external clock signal or supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator (see Figure 14. Typical application with 8 MHz crystal).

The external clock signal has to respect the I/O characteristics and follows the recommended clock input waveform (refer to Figure 13. HSE clock source timing diagram).

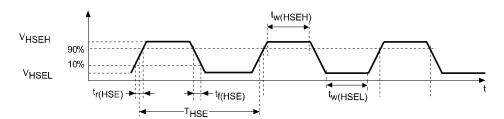
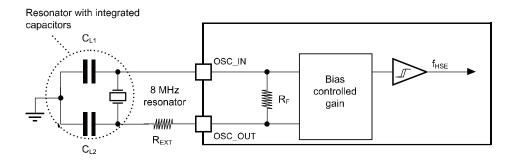


Figure 13. HSE clock source timing diagram

Figure 14. Typical application with 8 MHz crystal



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In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. The R_{EXT} value depends on the crystal characteristics (refer to the crystal resonator manufacturer for more details on them).

6.6.4 Advanced-control timer (TIM1)

The advanced-control timer (TIM1) can be seen as a three-phase PWM multiplexed on six channels. It has complementary PWM outputs with programmable inserted deadtimes.

This timer is used to generate the PWM signal for the three half-bridge gate drivers as shown in Table 10. TIM1 channel configuration.

MCU I/O **Analog IC input TIM1** channel **PB13** LS1 TIM1_CH1N PB14 LS2 TIM1_CH2N PB15 LS3 TIM1_CH3N HS₁ PA8 TIM1_CH1 PA9 HS2 TIM1_CH2 PA10 HS3 TIM1 CH3

Table 10. TIM1 channel configuration

6.7 Test mode

A dedicated pin TESTMODE is available to enter into the test mode.

Note: In the application, the TESTMODE pin should be shorted to GND in order not to enter the test mode inadvertently.

6.8 Operational amplifier

The device integrates a rail-to-rail operational amplifier suitable for signal conditioning, in particular for current sensing.

The operational amplifier provides a rail-to-rail output stage with fast recovery in the saturation condition. The output stage saturation happens in linear applications when a high amplitude input signal occurs and causes the output of the operational amplifier to move outside its real capabilities.

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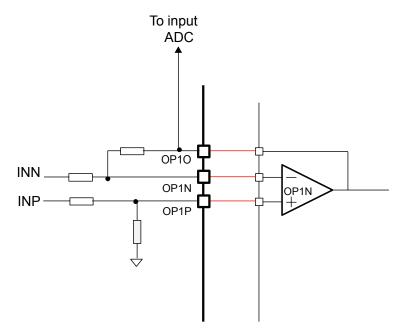


Figure 15. Operational amplifier

6.9 Comparator

A comparator is available to perform an overcurrent protection. The OC Comp pin can be connected to the shunt resistor to monitor the load current, the internal OC threshold can be set via MCU (PF6 and PF7 port, see Table 12. OC threshold values).

When an OC event is triggered, the OC comparator output signals the OC event to the PB12 and PA12 inputs of MCU (BKIN and ETR).

Depending on the status of the OC_SEL signal (see Table 11. OC protection selection) the OC event is acting directly on the control logic of the gate driver switching off all high-side gate outputs, and consequently the external high-side power switches.

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Figure 16. Comparator

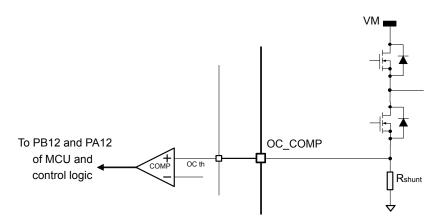


Table 11. OC protection selection

OC_SEL (PA11)	Function
0	OC comparator output signal is visible only to MCU (default)
1	OC comparator output signal is visible to MCU and also acts on gate driver control logic

Table 12. OC threshold values

OC_TH_STBY2 (PF6)	OC_TH_STBY1 (PF7)	OC threshold [mV]	Note
0	0	NΛ	Standby mode
U	U	N.A. (see Section 6.4 Standle	(see Section 6.4 Standby mode)
0	1	100	-
1	0	250	-
1	1	500	-

When the overcurrent condition disappears, the latched overcurrent signal is released only after all the high-side outputs are kept low for at least $t_{OCrelease}$ time. (Refer to Figure 17. Driver logic overcurrent management signals).

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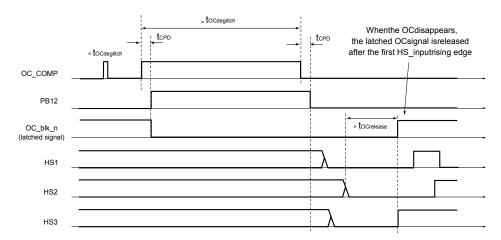


Figure 17. Driver logic overcurrent management signals

ESD protection strategy 6.10

clamp

GND

VDD(3.3 V) AnalogI/O DigitalI/O GND VM(45 VMAX.) VBOOT Linear reg. POWER POWER -CA POWER HVU/V/W ESD active clamp REG OUT - POWER High-side driver(X3) LVU/V/W ESD active

POWER

Low- sidedriver(X3)

Figure 18. ESD protection strategy

- sw

ESD active clamp

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BELOW GND



7 Application example

Figure 19. Application example shows an application example using the STSPIN32F0B device to drive a three-phase motor with single shunt configuration and digital Hall effect sensors. The others features implemented are:

- VDD (3.3 V) power supply internally generated via DC/DC regulator
- VREG12 (12 V) power supply internally generated via LDO linear regulator
- USART serial interface (PB6 and PB7)
- Serial wire debug ports (PA13 SWD IO, PA14 SWD CLK)
- Ready and alarm lines (PF0, PF1)
- · Reset dedicated pin
- Overcurrent protection using internal comparator
- Current sensing using operational amplifier and ADC (PA5)
- Digital Hall effect sensors decoding (PA0, PA1, PA2)
- Bus voltage compensation using internal ADC (PA3)
- Application temperature monitoring using internal ADC (PA4)

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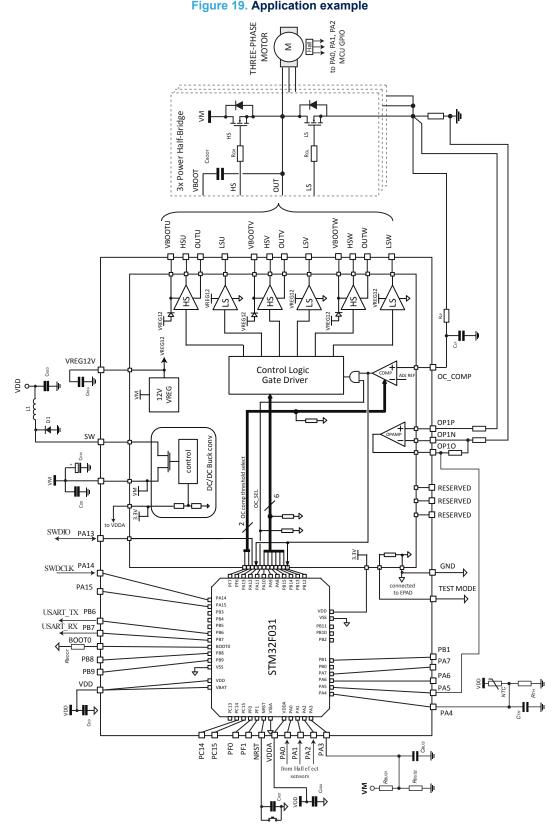


Figure 19. Application example

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8 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

A customized VFQFPN48 7 x 7 package is proposed. A smaller EPAD, internally connected to the ground pin, is desired to place through holes on the bottom of the package.

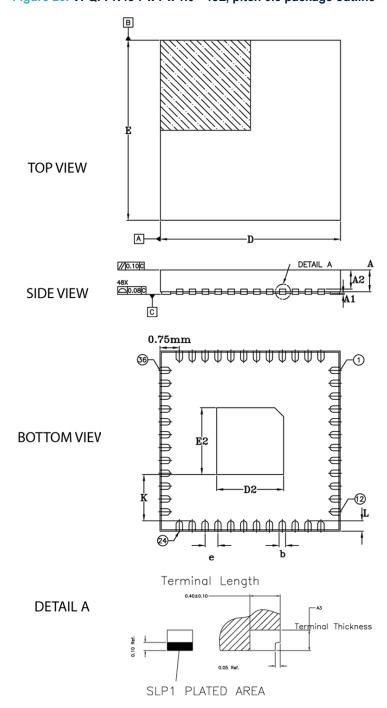
Lead plating is Nickel/Palladium/Gold (Ni/Pd/Au).

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8.1 VFQFPN48 7 x 7 package information

Figure 20. VFQFPN48 7 x 7 x 1.0 - 48L, pitch 0.5 package outline



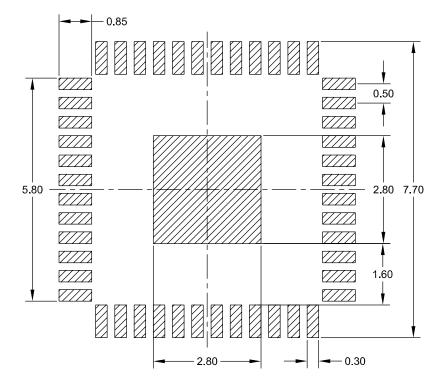
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Table 13. VFQFPN48 7 x 7 x 1.0 - 48L, pitch 0.5 - package mechanical data

Symbol	Dimensions (mm)			
Зуший	Min.	Тур.	Max.	
А	0.90	0.95	1.00	
A1	0.0	-	0.05	
A2		0.75		
A3		0.203		
b	0.20	0.25	0.30	
D	6.90	7.00	7.10	
E	6.90	7.00	7.10	
е		0.50		
D2	2.50	2.60	2.70	
E2	2.50	2.60	2.70	
К	1.80			
L	0.30	0.40	0.50	

Figure 21. VFQFPN48 7 x 7 x 1.0 - 48L, pitch 0.5 - suggested footprint



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Revision history

Table 14. Document revision history

Date	Revision	Changes
18-Feb-2019	1	Initial release.

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